

Description

The BSO130P03SH uses advanced trench technology

to provide excellent R_{DS(ON)}, low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



SOP-8

General Features

 $V_{DS} = -30V I_{D} = -12A$

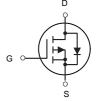
 $R_{DS(ON)}$ < 13m Ω @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
BSO130P03SH	SOP-8	HXY MOSFET	3000

Absolute Maximum Ratings(Tc=25℃ unless otherwise noted)

Symbol	Parameter	Rating	Units	
V _{DS}	Drain-Source Voltage	-30	V	
Vgs	Gate-Source Voltage	<u>+</u> 20	V	
I _D @T _A =25°C	Drain Current³, V _{GS} @ 10V	-12	А	
I _D @T _A =70°C	Drain Current ³ , V _{GS} @ 10V	-9.1	А	
Ідм	Pulsed Drain Current ¹	-40	Α	
P _D @T _A =25°C	Total Power Dissipation	2.5	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
Rthj-a	Maximum Thermal Resistance, Junction- ambient ³	50	°C/W	



Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
` '	Static Drain-Source On- Resistance ²	V _{GS} =-10V, I _D =-10A	-	10	13	mΩ
		V _{GS} =-4.5V, I _D =-6A	-	15	25	mΩ
V _G S(th)	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-	-2.5	V
g fs	Forward Transconductance	V _{DS} =-10V, I _D =-10A	-	22	-	S
IDSS	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V	-	-	-10	uA
Igss	Gate-Source Leakage	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Q_g	Total Gate Charge	I _D =-6A	-	28	45	nC
Q_{gs}	Gate-Source Charge	V _{DS} =-15V	-	7	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	11	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-15V	-	13	-	ns
t _r	Rise Time	I _D =-1A R _G =3.3Ω	-	10	-	ns
t _{d(off)}	Turn-off Delay Time		-	80	-	ns
t _f	Fall Time	V _{GS} =-10V	-	37	-	ns
Ciss	Input Capacitance	V _{GS} =0V V _{DS} =	-	2940	4700	pF
Coss	Output Capacitance	15V f=1.0MHz	-	290	-	pF
C _{rss}	Reverse Transfer Capacitance]	-	210	-	pF
Rg	Gate Resistance	f=1.0MHz	-	6.2	12.4	Ω
VsD	Forward On Voltage ²	I _S =-2.1A, V _{GS} =0V	-	-	-1.2	V
trr	Reverse Recovery Time	I _S =-10A, V _{GS} =0V, dI/dt=100A/µs	ı	19	-	ns
Q _{rr}	Reverse Recovery Charge		-	6	-	nC

Notes:

^{1.} Pulse width limited by Max. junction temperature.

² Pulse test

^{3.}Surface mounted on 1 in 2 copper pad of FR4 board, t \leq 10s; 125 °C/W when mounted on Min. copper pad.



Typical Characteristics

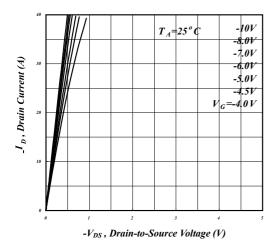


Fig 1. Typical Output Characteristics

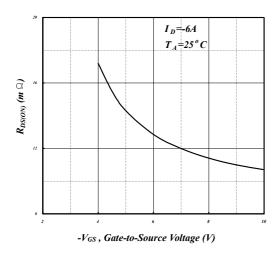
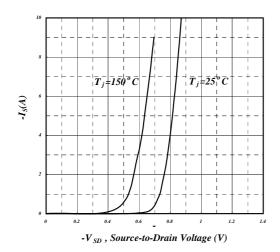


Fig 3. On-Resistance v.s. Gate Voltage



Reverse Diode

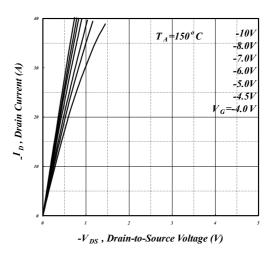


Fig 2 Typical Output Characteristics

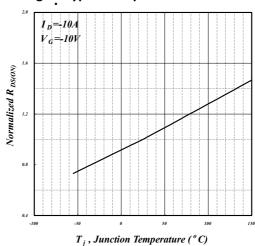


Fig 4. Normalized On-Resistance v.s. Junction Temperature

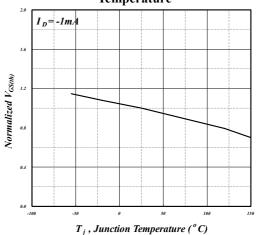


Fig 6. Gate Threshold Voltage v.s.
Junction Temperatur

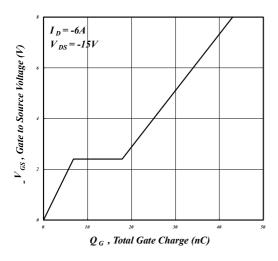


Fig 7. Gate Charge Characteristics

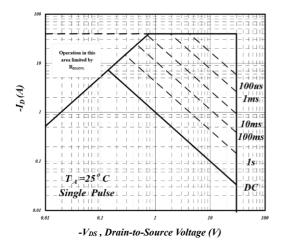


Fig 9. Maximum Safe Operating Area

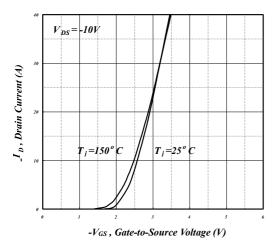


Fig 11. Transfer Characteristics

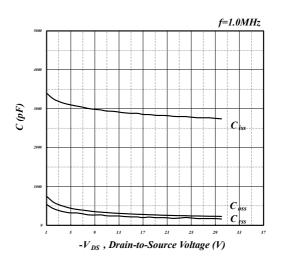


Fig 8. Typical Capacitance Characteristics

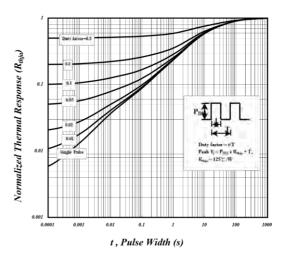


Fig 10. Effective Transient Thermal Impedance

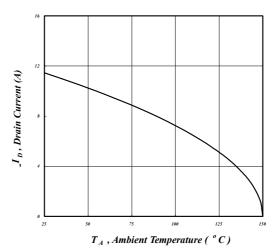
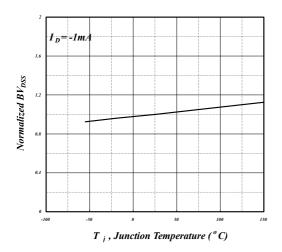


Fig 12. Drain Current v.s. Ambient Temperature



 $\label{eq:posterior} \mbox{Fig 13. Normalized BV}_{DSS} \ \ \mbox{v.s.} \\ \mbox{JunctionTemperature}$

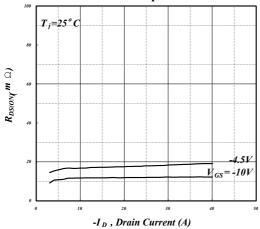


Fig 15. Typ. Drain-Source on State Resistance

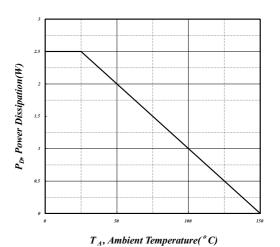
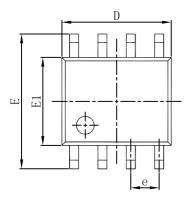
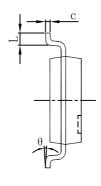


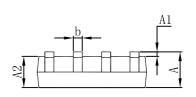
Fig 14. Total Power Dissipation



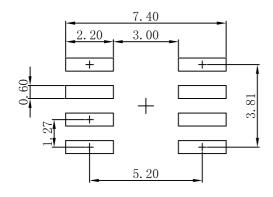
SOP-8 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	1.350	1.750	0.053	0.069	
A1	0.100	0. 250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
c	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0. 197	
e	1. 270 (BSC)	0.050 (BSC)		
E	5.800	6.200	0. 228	0. 244	
E1	3.800	4.000	0.150	0. 157	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



- Note: 1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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